

NP100T12P2T3

1200 V, 100 A, Power Integrated Module

Rev. 1 — 20 February 2024

Product data sheet

1. General description

IGBT power module provides ultra-low conduction loss as well as short circuit ruggedness. They are designed for applications such as inverters for motor drivers and servo drivers.

2. Features and benefits

- Low switching losses and low saturation voltage $V_{CE(sat)}$
- 10 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175 °C
- Low stray inductance package
- Fast and soft reverse recovery anti-parallel free-wheeling diode
- RoHS compliant product
- Integrated NTC thermistor temperature sensor

3. Applications

- Inverter for motor drivers and servo drivers
- AC/DC servo drive amplifier

4. Ordering information

Table 1. Ordering information

Type number	Package		
	Name	Description	Version
NP100T12P2T3	NP2-35P	plastic house; through hole solderable pin with copper baseplate; 35 pins; 62.5 mm × 122.5 mm × 17 mm body	SOT8053-1

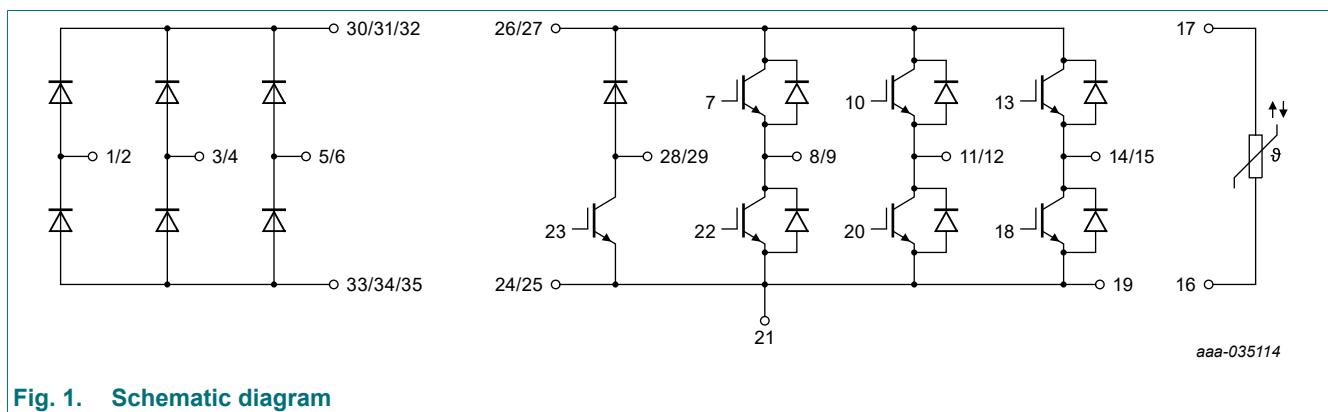


Fig. 1. Schematic diagram

5. Limiting values

Table 2. IGBT

Symbol	Parameter	Conditions	Min	Max	Unit
Inverter					
V_{CES}	collector-emitter voltage	$T_j = 25\text{ °C}$	-	1200	V
I_C	DC collector current	$T_{case} = 100\text{ °C}; T_{jmax} = 175\text{ °C}$	-	100	A
I_{CRM}	repetitive peak collector current	$t_p = 1\text{ ms}$	-	200	A
V_{GES}	gate to emitter voltage		-	±20	V
Brake-chopper					
V_{CES}	collector-emitter voltage	$T_j = 25\text{ °C}$	-	1200	V
I_C	DC collector current	$T_{case} = 100\text{ °C}; T_{jmax} = 175\text{ °C}$	-	50	A
I_{CRM}	repetitive peak collector current	$t_p = 1\text{ ms}$	-	100	A
V_{GES}	gate to emitter voltage		-	±20	V

Table 3. Diode

Symbol	Parameter	Conditions	Min	Max	Unit
Inverter					
V_{RRM}	repetitive peak reverse voltage	$T_j = 25\text{ °C}$	-	1200	V
I_F	continuous DC forward current	$T_{case} = 100\text{ °C}; T_{jmax} = 175\text{ °C}$	-	100	A
I_{FRM}	repetitive peak forward current	$t_p = 1\text{ ms}$	-	200	A
I^2t	I^2t -value	$V_R = 0\text{ V}; t_p = 10\text{ ms}; T_j = 125\text{ °C}$	-	1795	A ² s
		$V_R = 0\text{ V}; t_p = 10\text{ ms}; T_j = 150\text{ °C}$	-	1488	A ² s
Rectifier					
V_{RRM}	repetitive peak reverse voltage	$T_j = 25\text{ °C}$	-	1600	V
I_{FRMSM}	maximum RMS forward current per chip	$T_{case} = 100\text{ °C}$	-	100	A
I_{RMSM}	maximum RMS forward current at rectifier output	$T_{case} = 100\text{ °C}$	-	100	A
I_{FSM}	surge forward current	$t_p = 10\text{ ms}; T_j = 25\text{ °C}$	-	1272	A
		$t_p = 10\text{ ms}; T_j = 150\text{ °C}$	-	983	A
I^2t	I^2t -value	$t_p = 10\text{ ms}; T_j = 25\text{ °C}$	-	8099	A ² s
		$t_p = 10\text{ ms}; T_j = 150\text{ °C}$	-	4840	A ² s
Brake-chopper					
V_{RRM}	repetitive peak reverse voltage	$T_j = 25\text{ °C}$	-	1200	V
I_F	continuous DC forward current	$T_{case} = 100\text{ °C}; T_{jmax} = 175\text{ °C}$	-	50	A
I_{FRM}	repetitive peak forward current	$t_p = 1\text{ ms}$	-	100	A
I^2t	I^2t -value	$V_R = 0\text{ V}; t_p = 10\text{ ms}; T_j = 125\text{ °C}$	-	360	A ² s
		$V_R = 0\text{ V}; t_p = 10\text{ ms}; T_j = 150\text{ °C}$	-	336	A ² s

6. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$R_{th(j-c)}$	thermal resistance from junction to case	per IGBT	inverter	-	-	0.26	K/W
			brake-chopper	-	-	0.48	K/W
		per diode	inverter	-	-	0.45	K/W
			rectifier	-	-	0.36	K/W
			brake-chopper	-	-	1.2	K/W

7. Electrical characteristics

Table 5. IGBT

$T_j = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
Inverter							
BV_{CES}	collector-emitter breakdown voltage	$V_{GE} = 0\text{ V}$; $I_C = 1\text{ mA}$	1200	-	-	V	
I_{CES}	collector-emitter cutoff current	$V_{GE} = 0\text{ V}$; $V_{CE} = V_{CES}$	-	-	1	mA	
I_{GES}	gate leakage current	$V_{CE} = 0\text{ V}$; $V_{GE} = V_{GES}$	-	-	± 500	nA	
$V_{GE(th)}$	gate emitter threshold voltage	$V_{CE} = 10\text{ V}$; $I_C = 3.8\text{ mA}$	5	6.0	6.8	V	
R_G	internal gate resistor	$f = 1\text{ MHz}$	-	9.1	-	Ω	
$V_{CE(sat)}$	collector-emitter saturation voltage	$I_C = 100\text{ A}$; $V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}$	-	1.65	1.95	V
			$T_j = 125\text{ °C}$	-	1.8	-	V
			$T_j = 150\text{ °C}$	-	1.85	-	V
C_{ies}	input capacitance	$V_{GE} = 0\text{ V}$; $V_{CE} = 25\text{ V}$; $f = 100\text{ kHz}$	-	8.2	-	nF	
C_{oes}	output capacitance		-	1.51	-	nF	
C_{res}	reverse transfer capacitance		-	0.29	-	nF	
Q_g	total gate charge	$V_{CC} = 960\text{ V}$; $I_C = 100\text{ A}$; $V_{GE} = \pm 15\text{ V}$	-	0.57	-	μC	
$t_{d(on)}$	turn-on delay time	$V_{CC} = 600\text{ V}$; $I_C = 100\text{ A}$; $V_{GE} = \pm 15\text{ V}$; $R_{Gon} = 1.5\text{ }\Omega$; $R_{Goff} = 1.5\text{ }\Omega$; $L_S = 50\text{ nH}$	$T_j = 25\text{ °C}$	-	122	-	ns
			$T_j = 125\text{ °C}$	-	129	-	ns
			$T_j = 150\text{ °C}$	-	136	-	ns
t_r	rise time		$T_j = 25\text{ °C}$	-	23	-	ns
			$T_j = 125\text{ °C}$	-	25	-	ns
			$T_j = 150\text{ °C}$	-	26	-	ns
$t_{d(off)}$	turn-off delay time		$T_j = 25\text{ °C}$	-	231	-	ns
			$T_j = 125\text{ °C}$	-	288	-	ns
			$T_j = 150\text{ °C}$	-	304	-	ns
t_f	fall time	$T_j = 25\text{ °C}$	-	134	-	ns	
		$T_j = 125\text{ °C}$	-	215	-	ns	
		$T_j = 150\text{ °C}$	-	216	-	ns	

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
E _{on}	turn-on switching loss	V _{CC} = 600 V; I _C = 100 A; V _{GE} = ±15 V; R _{Gon} = 1.5 Ω; L _S = 50 nH; di/dt = 4500 A/μs	T _j = 25°C	-	5.3	-	mJ
			T _j = 125°C	-	8.7	-	mJ
			T _j = 150°C	-	10	-	mJ
E _{off}	turn-off switching loss	V _{CC} = 600 V; I _C = 100 A; V _{GE} = ±15 V; R _{Goff} = 1.5 Ω; L _S = 50 nH; du/dt = 5790 V/μs	T _j = 25°C	-	5.1	-	mJ
			T _j = 125°C	-	7.7	-	mJ
			T _j = 150°C	-	8.8	-	mJ
I _{sc}	short circuit data	V _{GE} = 15 V; V _{CC} = 800 V; T _j = 150 °C; t _p ≤ 10 μs	T _j = 150°C	-	397	-	A
R _{th(j-c)}	thermal resistance, junction to case	per IGBT	-	-	0.26	K/W	
T _{jop}	operating junction temperature		-40	-	150	°C	
Brake-chopper							
BV _{CES}	collector-emitter breakdown voltage	V _{GE} = 0 V; I _C = 1 mA		1200	-	-	V
I _{CES}	collector-emitter cutoff current	V _{GE} = 0 V; V _{CE} = V _{CES}		-	-	1	mA
I _{GES}	gate leakage current	V _{CE} = 0 V; V _{GE} = V _{GES}		-	-	±500	nA
V _{GE(th)}	gate emitter threshold voltage	V _{CE} = 10 V; I _C = 1.7 mA		5	6.0	6.8	V
R _G	internal gate resistor	f = 1 MHz		-	7.1		Ω
V _{CE(sat)}	collector-emitter saturation voltage	I _C = 50 A; V _{GE} = 15 V	T _j = 25°C	-	1.65	1.95	V
			T _j = 125°C	-	1.8	-	V
			T _j = 150°C	-	1.85	-	V
C _{ies}	input capacitance	V _{GE} = 0 V; V _{CE} = 25 V; f = 100 kHz		-	3.65	-	nF
C _{oes}	output capacitance			-	0.72	-	nF
C _{res}	reverse transfer capacitance			-	0.12	-	nF
Q _g	total gate charge	V _{CC} = 960 V; I _C = 50 A; V _{GE} = ±15 V		-	0.26	-	μC
t _{d(on)}	turn-on delay time	V _{CC} = 600 V; I _C = 50 A; V _{GE} = ±15 V; R _{Gon} = 15 Ω; R _{Goff} = 15 Ω; L _S = 50 nH	T _j = 25°C	-	64	-	ns
			T _j = 125°C	-	65	-	ns
			T _j = 150°C	-	67	-	ns
t _r	rise time		T _j = 25°C	-	31	-	ns
			T _j = 125°C	-	66	-	ns
			T _j = 150°C	-	68	-	ns
t _{d(off)}	turn-off delay time		T _j = 25°C	-	147	-	ns
			T _j = 125°C	-	178	-	ns
			T _j = 150°C	-	187	-	ns
t _f	fall time	T _j = 25°C	-	144	-	ns	
		T _j = 125°C	-	196	-	ns	
		T _j = 150°C	-	213	-	ns	

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
E _{on}	turn-on switching loss	V _{CC} = 600 V; I _C = 50 A; V _{GE} = ±15 V; R _{Gon} = 15 Ω; L _S = 50 nH; dI/dt = 1590 A/μs	T _j = 25°C	-	5.1	-	mJ
			T _j = 125°C	-	7.2	-	mJ
			T _j = 150°C	-	8.2	-	mJ
E _{off}	turn-off switching loss	V _{CC} = 600 V; I _C = 50 A; V _{GE} = ±15 V; R _{Goff} = 15 Ω; L _S = 50 nH; dV/dt = 6040 V/μs	T _j = 25°C	-	1.93	-	mJ
			T _j = 125°C	-	2.59	-	mJ
			T _j = 150°C	-	2.81	-	mJ
I _{sc}	short circuit data	V _{GE} = 15 V; V _{CC} = 800 V; T _j = 150 °C; t _p ≤ 10 μs	-	167	-	A	
R _{th(j-c)}	thermal resistance, junction to case	per IGBT	-	-	0.48	K/W	
T _{jop}	operating junction temperature		-40	-	150	°C	

Table 6. Diode

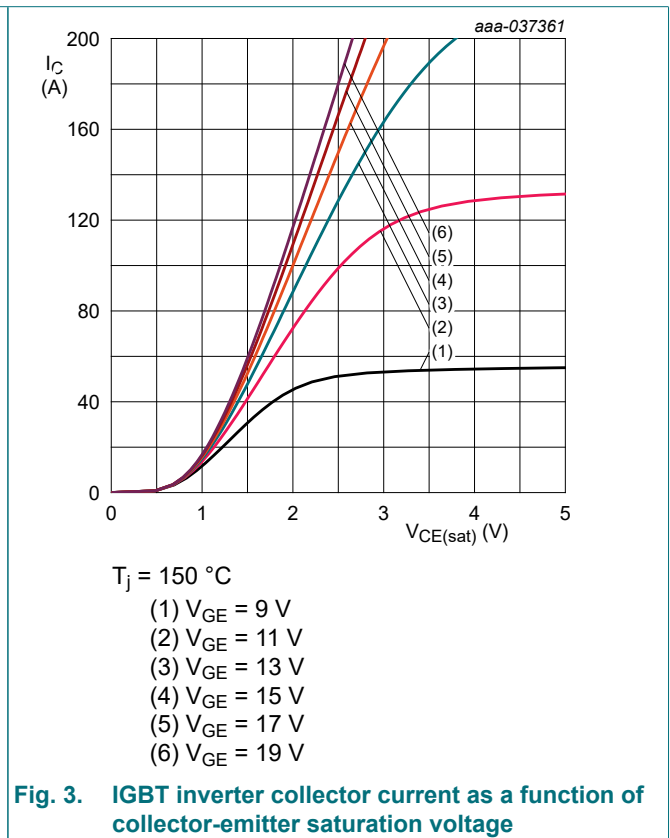
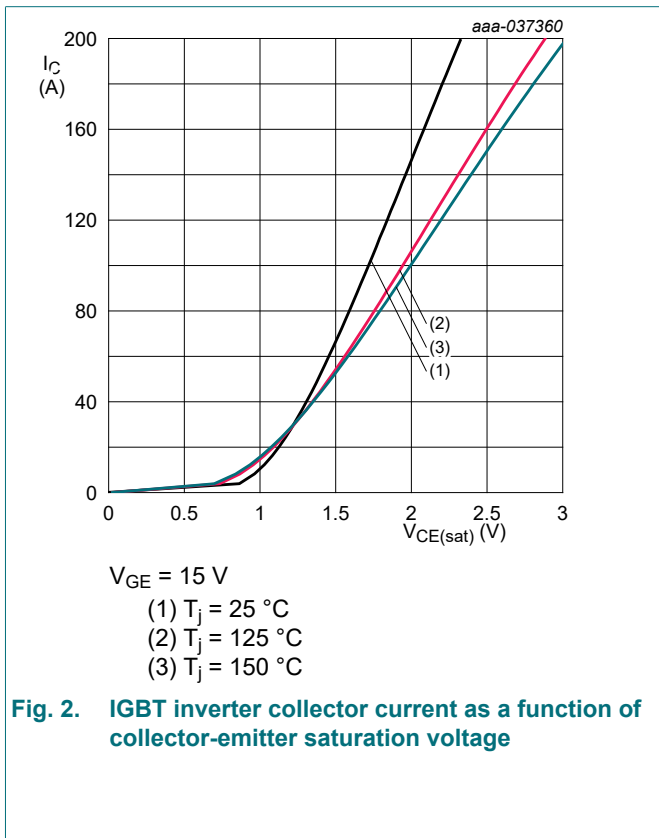
T_j = 25 °C unless otherwise specified.

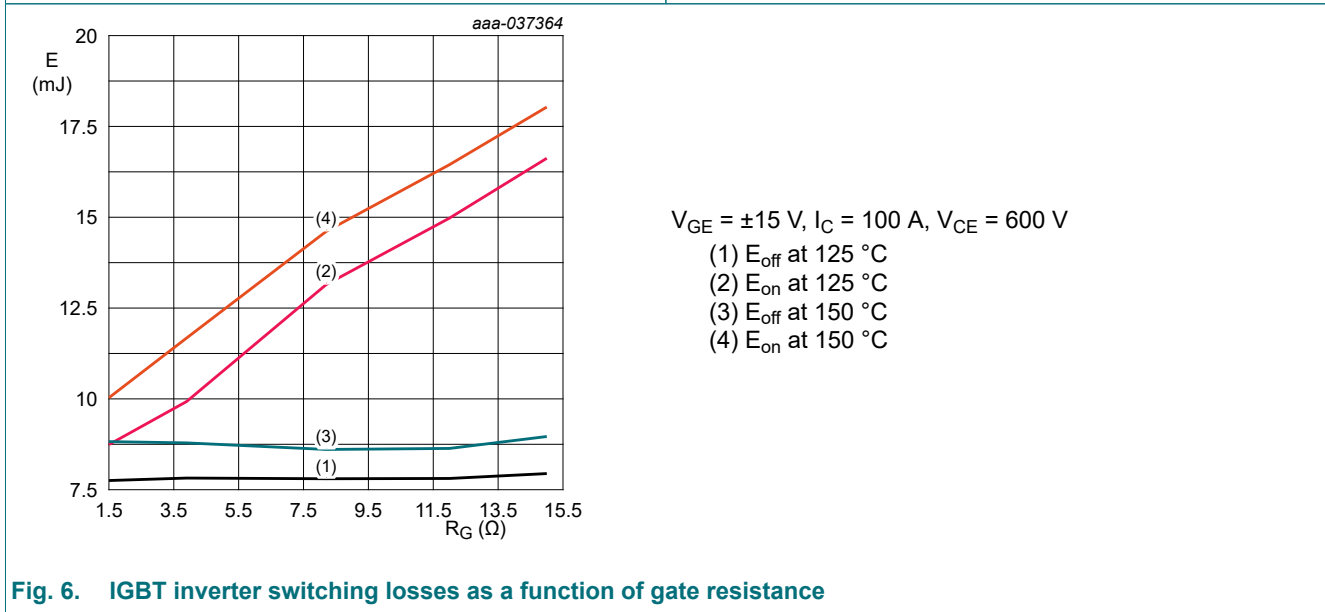
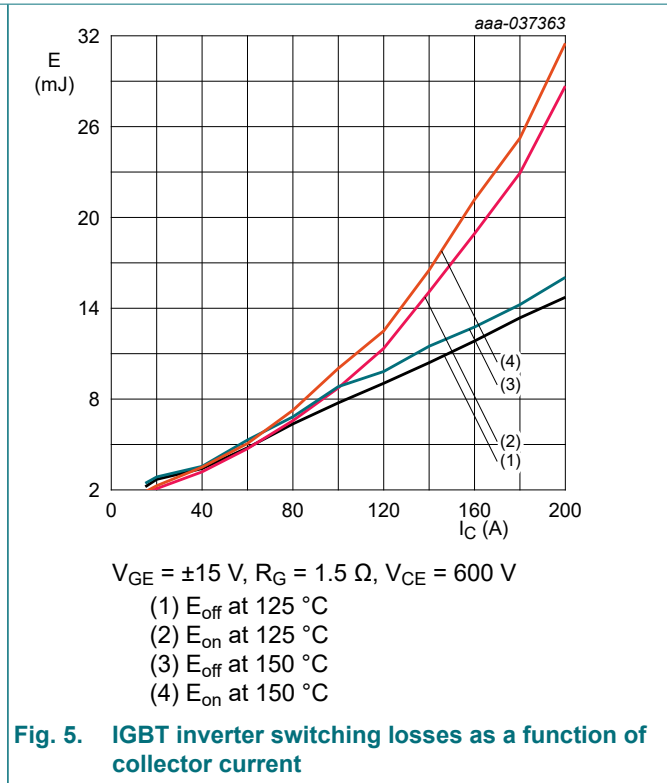
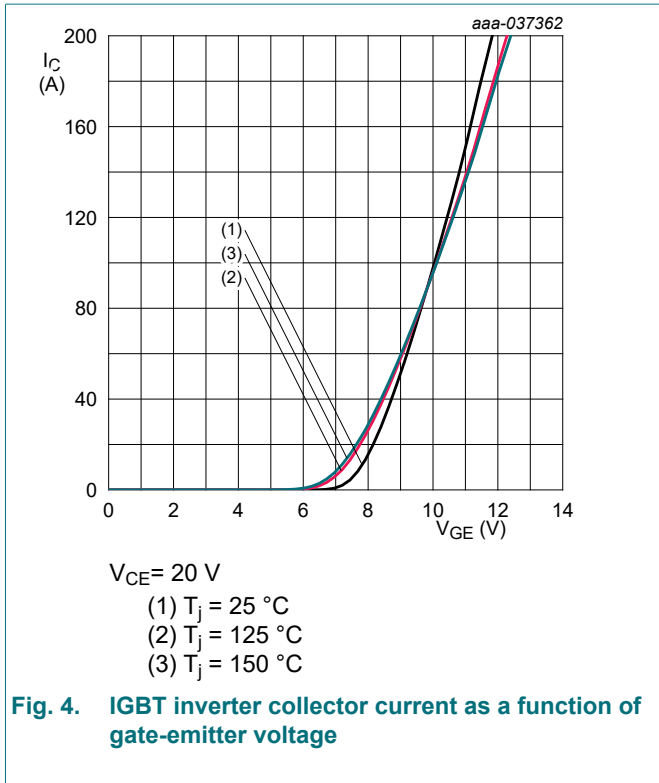
Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
Inverter							
V _F	forward voltage	I _F = 100 A	T _j = 25°C	-	1.7	2.1	V
			T _j = 125°C	-	1.7	-	V
			T _j = 150°C	-	1.7	-	V
I _{rr}	peak reverse recovery current	I _F = 100 A; V _R = 600 V ; -dI _F /dt = 2630 A/us; V _{GE} = -15 V	T _j = 25°C	-	126	-	A
			T _j = 125°C	-	130	-	A
			T _j = 150°C	-	132	-	A
Q _{rr}	reverse recovery charge	I _F = 100 A; V _R = 600 V ; -dI _F /dt = 2630 A/us; V _{GE} = -15 V	T _j = 25°C	-	6.48	-	μC
			T _j = 125°C	-	12.8	-	μC
			T _j = 150°C	-	15.4	-	μC
t _{rr}	reverse recovery time	I _F = 100 A; V _R = 600 V ; -dI _F /dt = 2630 A/us; V _{GE} = -15 V	T _j = 25°C	-	344	-	ns
			T _j = 125°C	-	515	-	ns
			T _j = 150°C	-	538	-	ns
E _{rec}	reverse recovery energy	I _F = 100 A; V _R = 600 V ; -dI _F /dt = 2630 A/us; V _{GE} = -15 V	T _j = 25°C	-	1.75	-	mJ
			T _j = 125°C	-	4.3	-	mJ
			T _j = 150°C	-	5.2	-	mJ
R _{th(j-c)}	thermal resistance, junction to case	per diode	-	-	0.45	K/W	
T _{jop}	operating junction temperature		-40	-	150	°C	
Rectifier							
V _F	forward voltage	I _F = 100 A	T _j = 150°C	-	0.99	-	V
I _R	reverse current	V _R = 1600 V	T _j = 150°C	-	1.5	-	A
R _{th(j-c)}	Thermal resistance, junction to case	per diode		-	-	0.36	K/W
T _{jop}	operating junction temperature			-40	-	150	°C

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Brake-chopper							
V _F	forward voltage	I _F = 50 A	T _J = 25°C	-	1.74	2.1	V
			T _J = 125°C	-	1.88	-	V
			T _J = 150°C	-	1.86	-	V
I _{rr}	peak reverse recovery current	I _F = 50 A; V _R = 600 V ; -di _F /dt = 1510 A/us; V _{GE} = -15 V	T _J = 25°C	-	17	-	A
			T _J = 125°C	-	20	-	A
			T _J = 150°C	-	20	-	A
Q _{rr}	reverse recovery charge	I _F = 50 A; V _R = 600 V ; -di _F /dt = 1510 A/us; V _{GE} = -15 V	T _J = 25°C	-	3.04	-	μC
			T _J = 125°C	-	5.52	-	μC
			T _J = 150°C	-	6.29	-	μC
t _{rr}	reverse recovery time	I _F = 50 A; V _R = 600 V ; -di _F /dt = 1510 A/us; V _{GE} = -15 V	T _J = 25°C	-	363	-	ns
			T _J = 125°C	-	536	-	ns
			T _J = 150°C	-	616	-	ns
E _{rec}	reverse recovery energy	I _F = 50 A; V _R = 600 V ; -di _F /dt = 1510 A/us; V _{GE} = -15 V	T _J = 25°C	-	0.747	-	mJ
			T _J = 125°C	-	1.65	-	mJ
			T _J = 150°C	-	1.94	-	mJ
R _{th(j-c)}	thermal resistance, junction to case	per diode		-	-	1.2	K/W
T _{Jop}	operating junction temperature			-40	-	150	°C

7.1. Waveforms and output characteristics

Table 7.





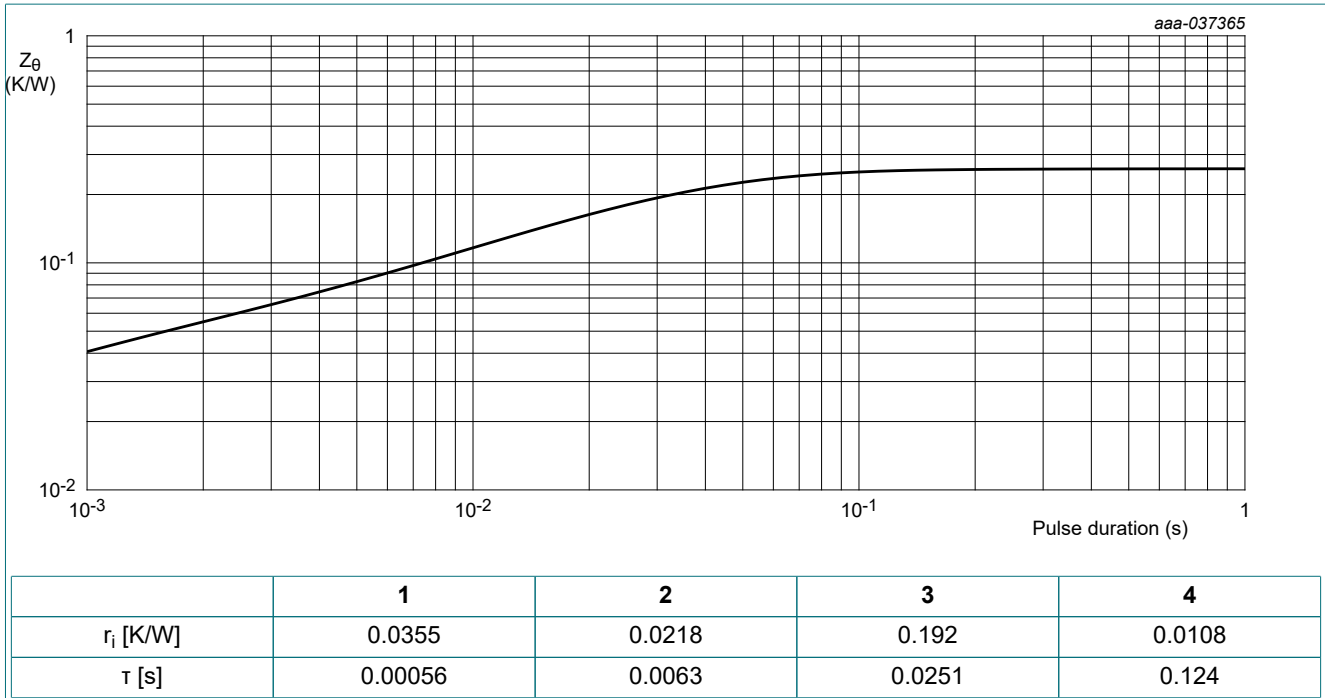


Fig. 7. Transient thermal impedance of IGBT inverter as a function of pulse duration

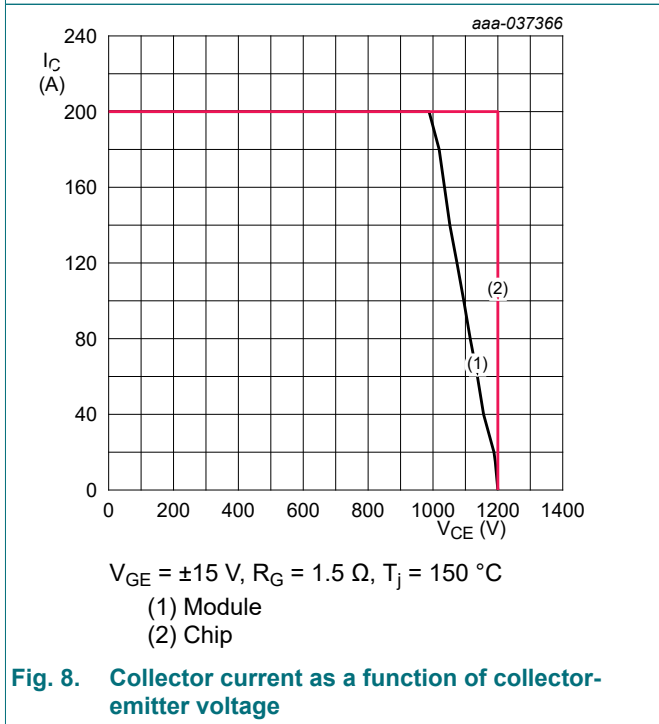


Fig. 8. Collector current as a function of collector-emitter voltage

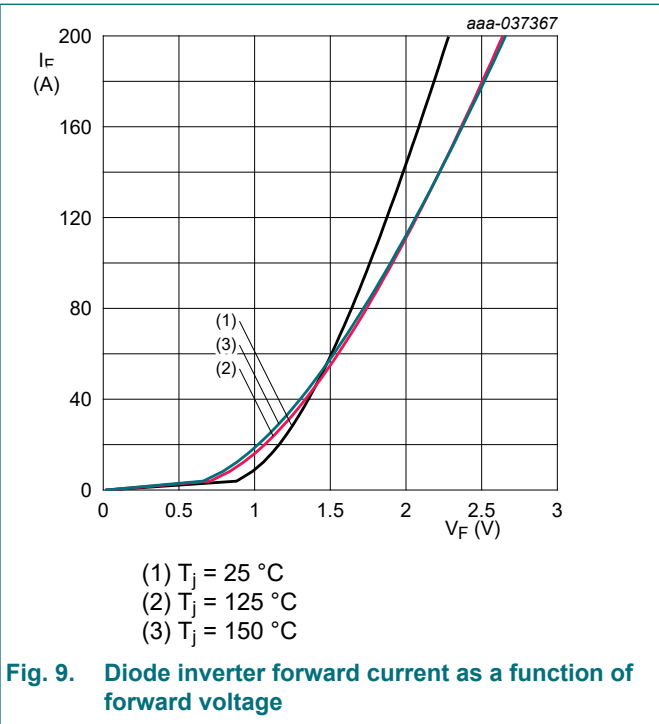


Fig. 9. Diode inverter forward current as a function of forward voltage

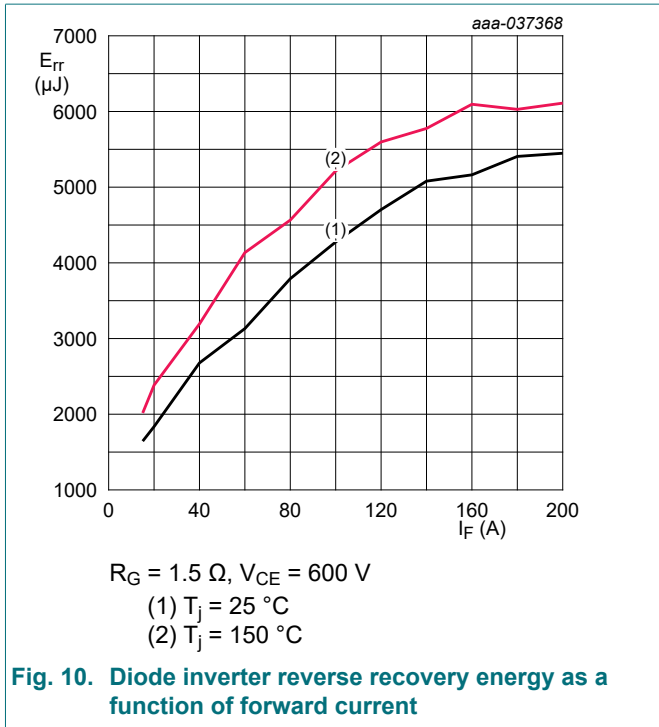


Fig. 10. Diode inverter reverse recovery energy as a function of forward current

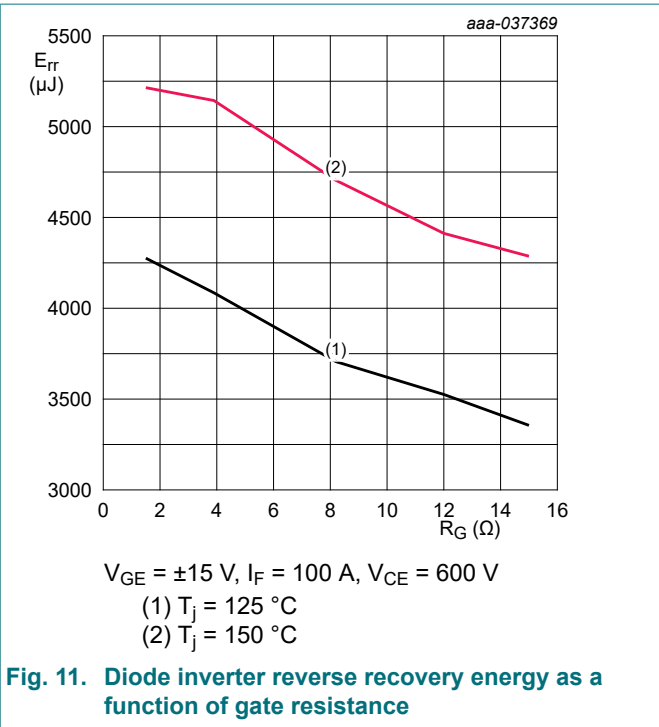


Fig. 11. Diode inverter reverse recovery energy as a function of gate resistance

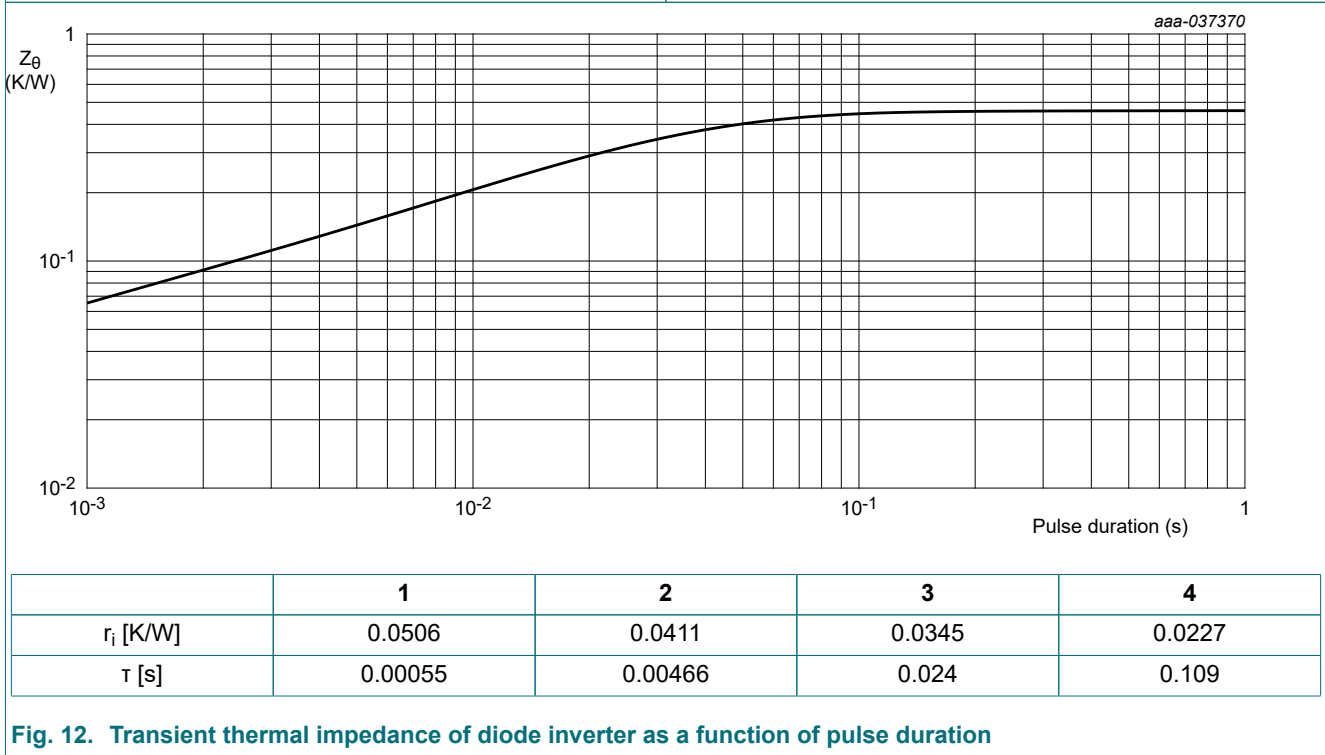
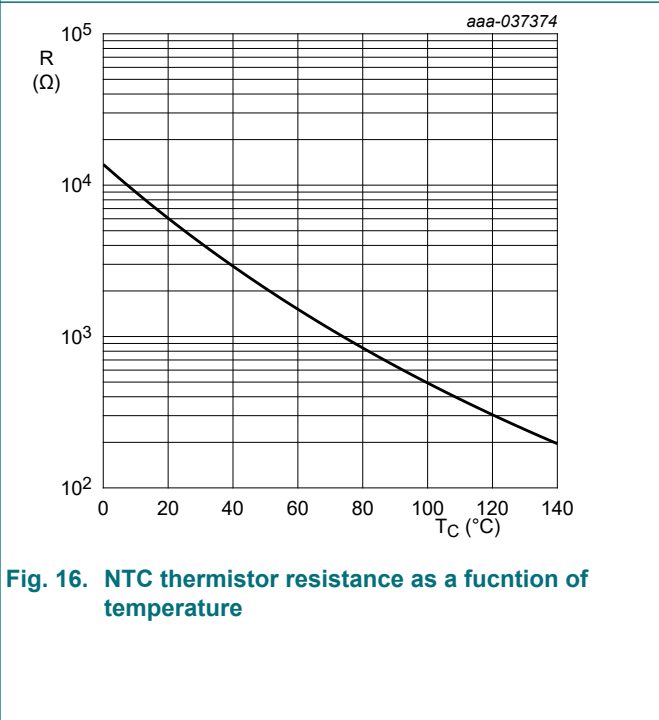
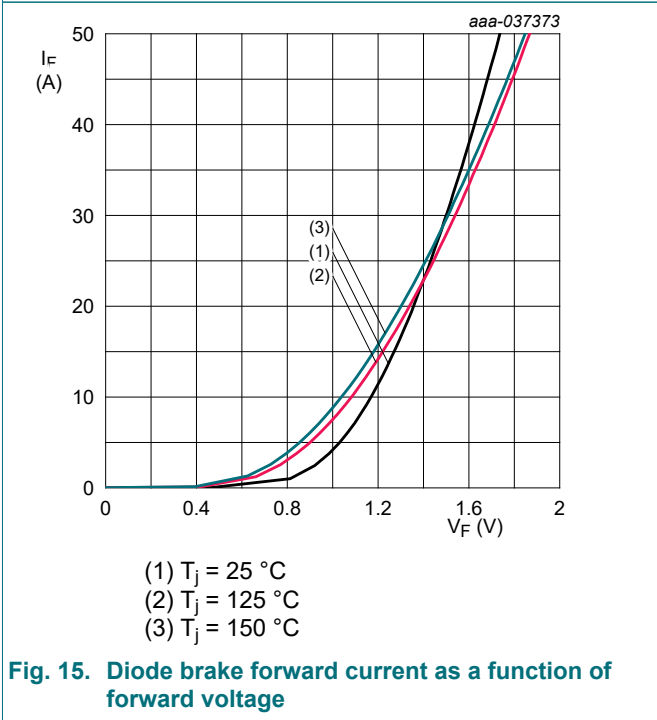
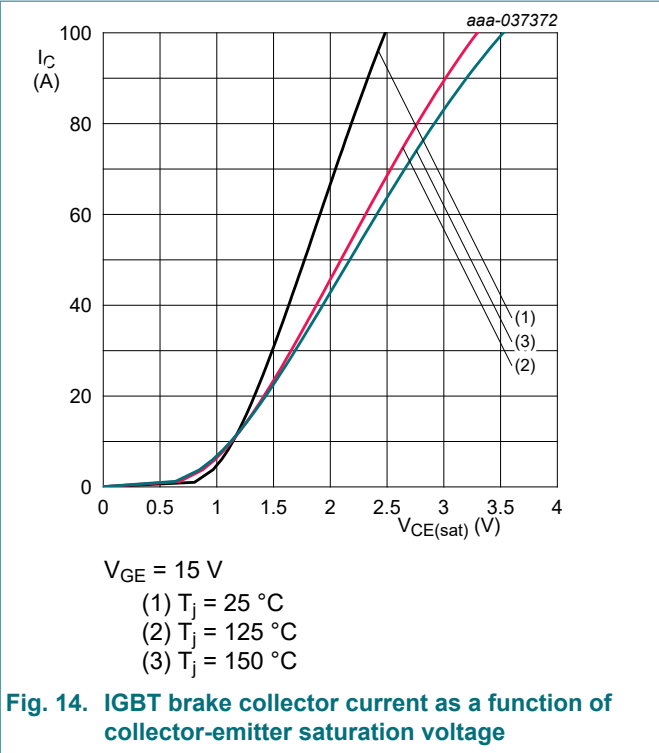
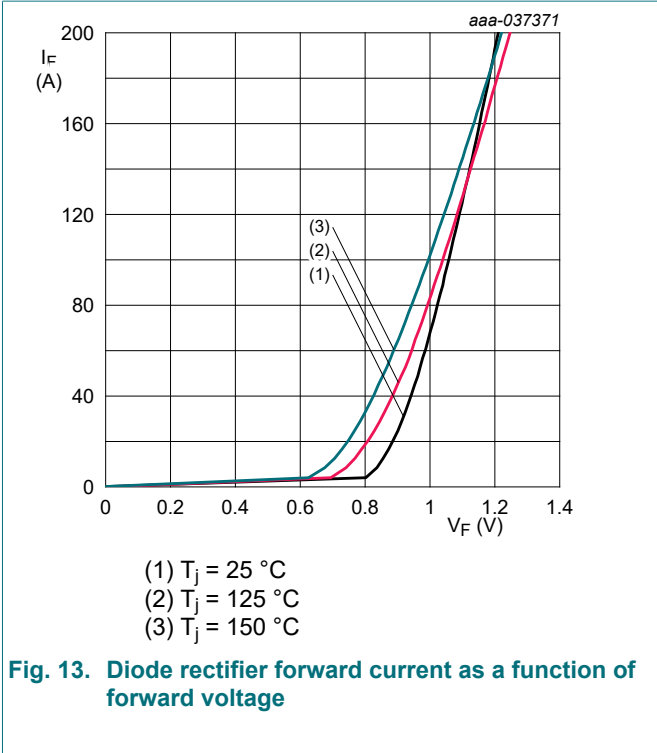


Fig. 12. Transient thermal impedance of diode inverter as a function of pulse duration



8. NTC thermistor

Table 8. NTC thermistor

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R ₂₅	rated resistance	T _{TNTC} = 25 °C	-	5	-	kΩ
ΔR/R	deviation of R100	T _{TNTC} = 100 °C; R ₁₀₀ = 493 Ω	-10	-	10	%
P ₂₅	power dissipation	T _{TNTC} = 25 °C	-	-	20	mW
B _{25/50}	B-value		-	3375	-	K
B _{25/80}	B-value		-	3414	-	K
B _{25/100}	V-value		-	3436	-	K

9. Module characteristics

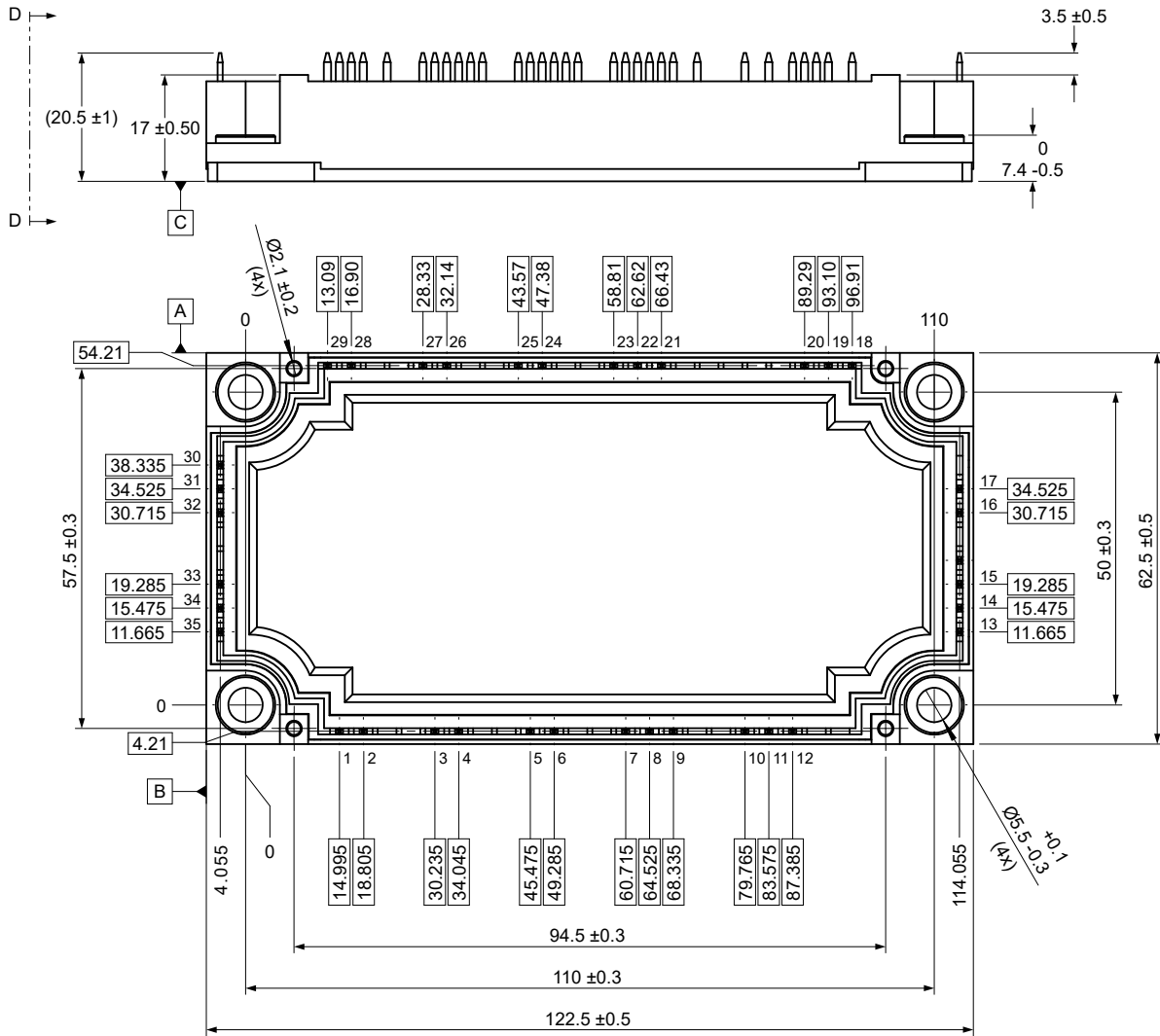
Table 9. Module characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{ISOL}	isolation test voltage	RMS; f = 50 Hz, t = 1 min	2.5	-	-	kV
	creepage distance	terminal to heat sink	-	10	-	mm
		terminal to terminal				mm
	clearance	terminal to heat sink	-	7.5	-	mm
		terminal to terminal				mm
CTI	comparative tracking index		-	>200	-	
L _{sCE}	stray inductance		-	35	-	nH
R _{CC'+EE'}	module lead resistance, terminal-chip	T _C = 25 °C per switch	-	1.2	-	mΩ
M	mounting torque for module mounting		-	-	-	Nm
G	weight		-	307	-	g
T _{stg}	storage temperature		-40	-	125	°C

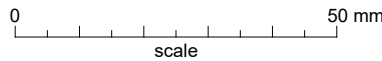
10. Package outline drawing

NP2-35P: plastic house, through hole solderable pin with copper baseplate, 35 pins; 62.5 mm x 122.5 mm x 17 mm body

SOT8053-1



Note: all pin position tolerance is ± 0.5 C A B



Dimensions (mm are the original dimensions)

sot8053-1_po

Outline version	References			European projection	Issue date
	IEC	JEDEC	EIAJ		
SOT8053-1					22-05-25 22-05-30

Fig. 17. Preliminary package outline drawing

11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NP100T12P2T3 v. 1	20240220	Product data sheet	-	-

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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